MCR310 Series

Preferred Device

Silicon Controlled Rectifiers

Reverse Blocking Triode Thyristors

Designed for industrial and consumer applications such as temperature, light and speed control; process and remote controls; warning systems; capacitive discharge circuits and MPU interface.

- Center Gate Geometry for Uniform Current Density
- All Diffused and Glass-Passivated Junctions for Parameter Uniformity and Stability
- Small, Rugged, Thermowatt Construction for Low Thermal Resistance, High Heat Dissipation and Durability
- Low Trigger Currents, 200 μA Maximum for Direct Driving from Integrated Circuits
- Pb-Free Packages are Available

MAXIMUM RATINGS (T_{.1} = 25°C unless otherwise noted.)

| Rating | Symbol | Value | Unit |
|--|--|-------------------|------------------|
| Peak Repetitive Forward and Reverse Blocking Voltage ⁽¹⁾ $ (T_J = -40 \text{ to } 110^{\circ}\text{C}) $ $ (1/2 \text{ Sine Wave, R}_{GK} = 1 \text{ k}\Omega) $ $ \text{MCR310-6} $ $ \text{MCR310-8} $ $ \text{MCR310-10} $ | V _{DRM} or V _{RRM} | 400 600 800 | Volts |
| On-State RMS Current (T _C = 75°C) | I _{T(RMS)} | 10 | Amps |
| Peak Non-repetitive Surge Current (1/2 Cycle, 60 Hz, T _J = -40 to 110°C) | I _{TSM} | 100 | Amps |
| Circuit Fusing (t = 8.3 ms) | l ² t | 40 | A ² s |
| Peak Gate Voltage (t ≤ 10 μs) | V_{GM} | ±5 | Volts |
| Peak Gate Current (t ≤ 10 μs) | I_{GM} | 1 | Amp |
| Peak Gate Power (t ≤ 10 μs) | P_{GM} | 5 | Watts |
| Average Gate Power | $P_{G(AV)}$ | 0.75 | Watt |
| Operating Junction Temperature Range | T_J | -40 to +110 | °C |
| Storage Temperature Range | T _{stg} | -40 to +150 | °C |
| Mounting Torque | _ | 8 | inlb. |

THERMAL CHARACTERISTICS

| Characteristic | Symbol | Max | Unit |
|---|-----------------|-----|------|
| Thermal Resistance, Junction to Case | $R_{\theta JC}$ | 2.2 | °C/W |
| Thermal Resistance, Junction to Ambient | $R_{\theta JA}$ | 60 | °C/W |

Maximum ratings are those values beyond which device damage can occur. Maximum ratings applied to the device are individual stress limit values (not normal operating conditions) and are not valid simultaneously. If these limits are exceeded, device functional operation is not implied, damage may occur and reliability may be affected.

(1) V_{DRM} and V_{RRM} for all types can be applied on a continuous basis. Ratings apply for zero or negative gate voltage; however, positive gate voltage shall not be applied concurrent with negative potential on the anode. Blocking voltages shall not be tested with a constant current source such that the voltage ratings of the devices are exceeded.

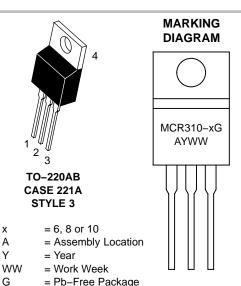


ON Semiconductor®

http://onsemi.com

SCRs 10 AMPERES RMS 400 thru 800 VOLTS





ORDERING INFORMATION

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| Device | Package | Shipping |
|------------|----------------------|----------|
| MCR310-6 | TO220AB | 500/Box |
| MCR310-6G | TO220AB (Pb-Free) | 500/Box |
| MCR310-8 | TO220AB | 500/Box |
| MCR310-8G | TO220AB (Pb-Free) | 500/Box |
| MCR310-10 | TO220AB | 500/Box |
| MCR310-10G | TO220AB (Pb-Free) | 500/Box |

Preferred devices are recommended choices for future use and best overall value.

MCR310 Series

ELECTRICAL CHARACTERISTICS ($T_C = 25^{\circ}C$, $R_{GK} = 1 \text{ k}\Omega$ unless otherwise noted)

| Characteristic | Symbol | Min | Тур | Max | Unit |
|--|------------------|---------|----------|-----------|----------|
| $\begin{array}{ll} \text{Peak Forward Blocking Current}^{(1)} & \text{$T_{\text{C}} = 110^{\circ}\text{C}$} \\ \text{$(T_{\text{J}} = 110^{\circ}\text{C}, V_{\text{D}} = \text{Rated V}_{\text{DRM}})$} & \text{$T_{\text{C}} = 25^{\circ}\text{C}$} \end{array}$ | I _{DRM} | _ _ | _ _ | 500 10 | μΑ μΑ |
| $ \begin{array}{cccccccccccccccccccccccccccccccccccc$ | I _{RRM} | _ _ | _ _ | 500 10 | μΑ μΑ |
| On-State Voltage (I _{TM} = 20 A Peak, Pulse Width ≤ 1 ms, Duty Cycle ≤ 2%) | V_{TM} | _ | 1.7 | 2.2 | Volts |
| Gate Trigger Current, Continuous $dc^{(2)}$ (V _D = 12 V, R _L = 100 Ω) | I _{GT} | _ | 30 | 200 | μΑ |
| Gate Trigger Voltage, Continuous dc $(V_D = 12 \text{ V}, \text{ R}_L = 100 \Omega)$ $(V_D = \text{Rated } V_{DRM}, \text{ R}_L = 10 \text{ k}\Omega, \text{ T}_J = 110^{\circ}\text{C})$ | V _{GT} | 0.1 | 0.5 — | 1.5 — | Volts |
| Holding Current (V _D = 12 V, I _{TM} = 100 mA) | l _Η | _ | _ | 6 | mA |
| Critical Rate of Rise of Forward Blocking Voltage (V _D = Rated V _{DRM} , T _J = 110°C, Exponential Waveform) | dv/dt | _ | 10 | | V/μs |
| Gate Controlled Turn-On Time $(V_D = Rated \ V_{DRM}, I_{TM} = 20 \ A, I_G = 2 \ mA)$ | t _{gt} | _ | 1 | _ | μs |

^{1.} Ratings apply for negative gate voltage or R_{GK} = 1 kΩ. Devices shall not have a positive gate voltage concurrently with a negative voltage on the anode. Devices should not be tested with a constant current source for forward and reverse blocking capability such that the voltage applied exceeds the rated blocking voltage.



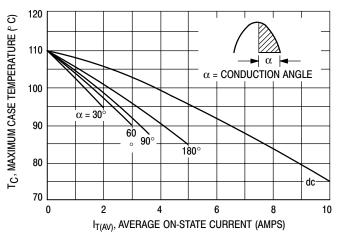


Figure 1. Average Current Derating

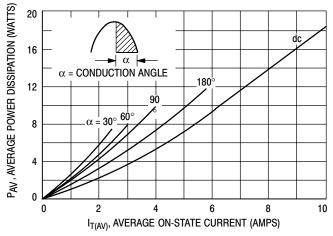


Figure 2. On-State Power Dissipation

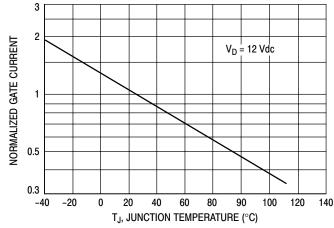


Figure 3. Normalized Gate Current

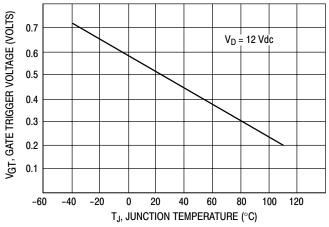
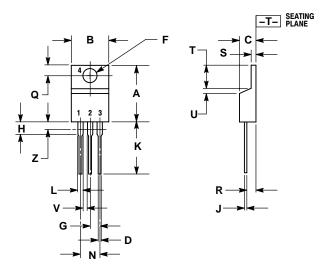


Figure 4. Gate Voltage

MCR310 Series

PACKAGE DIMENSIONS

TO-220AB CASE 221A-09 **ISSUE AA**



NOTES:

- DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
- CONTROLLING DIMENSION: INCH. DIMENSION Z DEFINES A ZONE WHERE ALL BODY AND LEAD IRREGULARITIES ARE ALLOWED.

| | INCHES | | MILLIN | IETERS |
|-----|--------|-------|--------|--------|
| DIM | MIN | MAX | MIN | MAX |
| Α | 0.570 | 0.620 | 14.48 | 15.75 |
| В | 0.380 | 0.405 | 9.66 | 10.28 |
| С | 0.160 | 0.190 | 4.07 | 4.82 |
| D | 0.025 | 0.035 | 0.64 | 0.88 |
| F | 0.142 | 0.147 | 3.61 | 3.73 |
| G | 0.095 | 0.105 | 2.42 | 2.66 |
| Н | 0.110 | 0.155 | 2.80 | 3.93 |
| J | 0.018 | 0.025 | 0.46 | 0.64 |
| K | 0.500 | 0.562 | 12.70 | 14.27 |
| L | 0.045 | 0.060 | 1.15 | 1.52 |
| N | 0.190 | 0.210 | 4.83 | 5.33 |
| Q | 0.100 | 0.120 | 2.54 | 3.04 |
| R | 0.080 | 0.110 | 2.04 | 2.79 |
| S | 0.045 | 0.055 | 1.15 | 1.39 |
| T | 0.235 | 0.255 | 5.97 | 6.47 |
| U | 0.000 | 0.050 | 0.00 | 1.27 |
| ٧ | 0.045 | | 1.15 | |
| Z | | 0.080 | | 2.04 |

PIN 1. CATHODE

2. ANODE

GATE

ANODE

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